

FIG. 1A

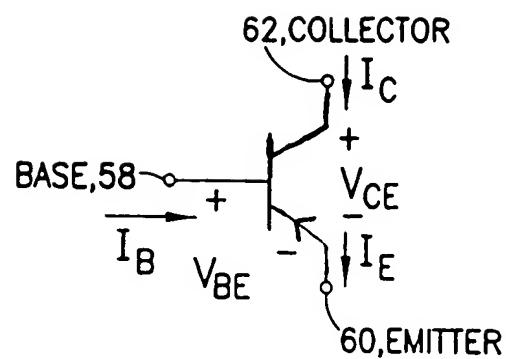


FIG. 1B

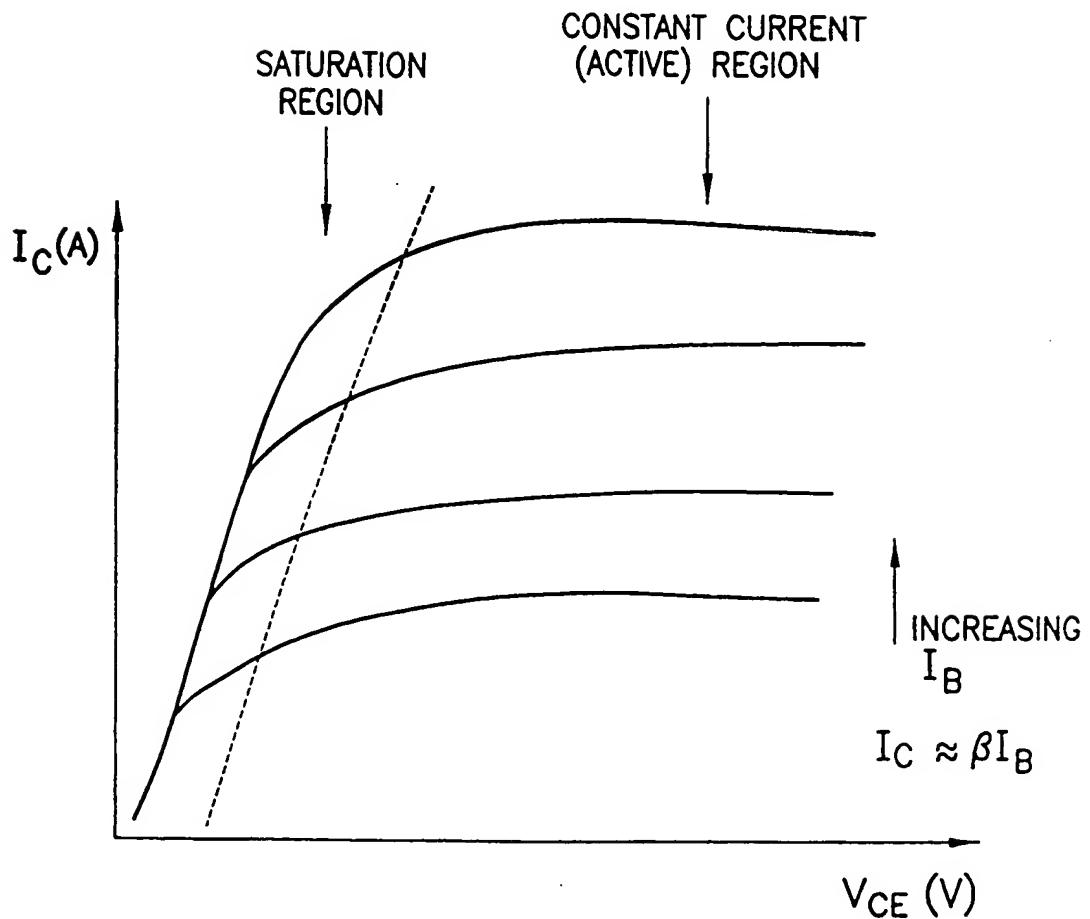


FIG. 1C

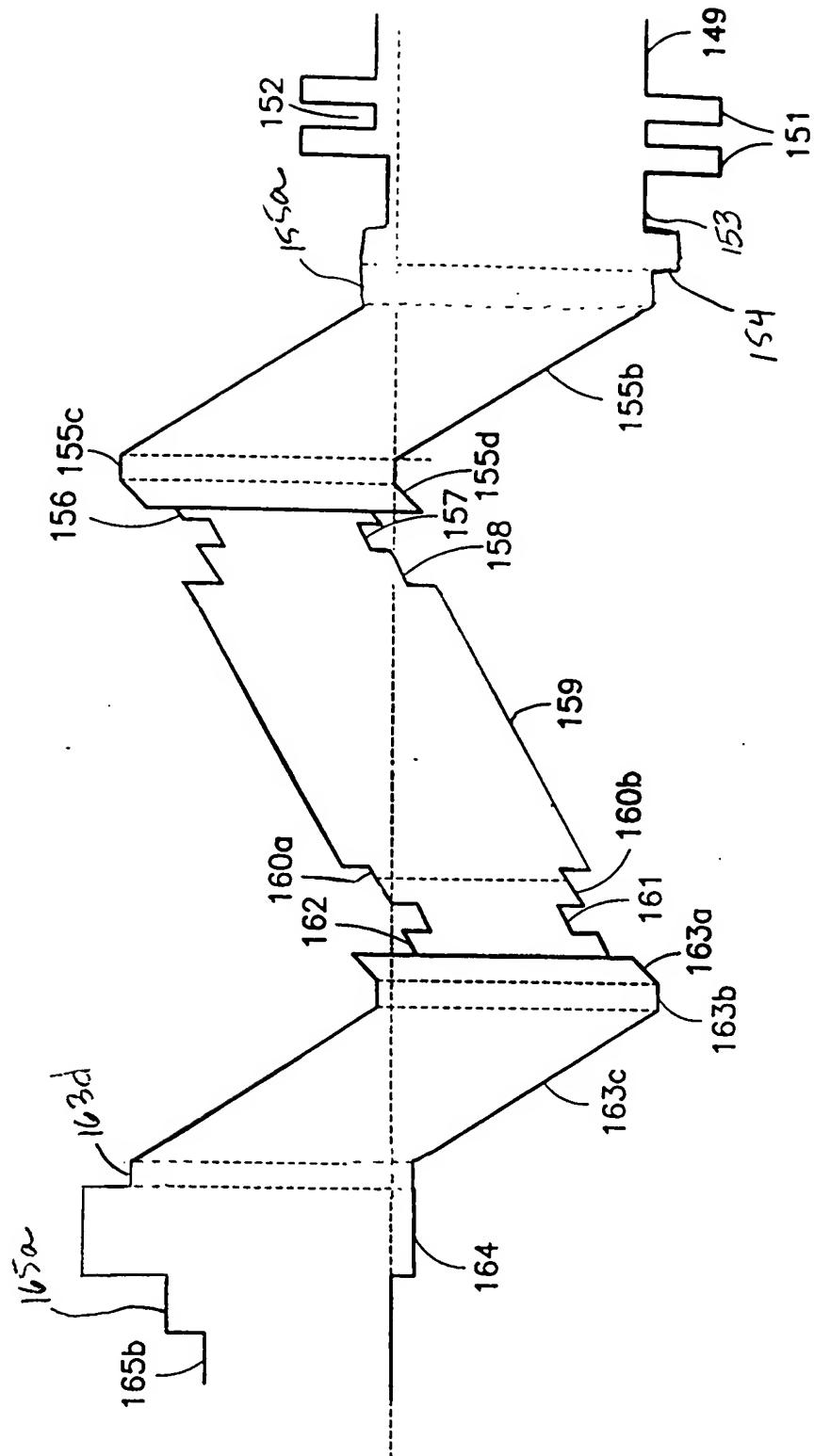
Layer Material	Layer Doping Type	Typical Doping Concentration (atoms/cm ³)	Typical Layer Thickness (Å)	Layer #
InGaAs	P+	1E20	25	165b
GaAs	P+	1E20	75	165a
Al(0.7)Ga(0.3)As	P	1E17	700	164b
Al(0.7)Ga(0.3)As	P+	1E19	10	164a
Al(.15)Ga(.85)As	P+	3.5E18	25	163d
Al(.15)Ga(.85)As	und	und	200 - 300	163c
Al(.15)Ga(.85)As	N+	3.5E18	80	163b
Al(.15)Ga(.85)As	und	und	20-30	163a
GaAs	und	und	15	162
In(.20)Ga(.80)AsN	und	und	60	161
GaAs	3	und	100	160b
GaAs	und	und	100 - 250	160a
Al(.15)Ga(.85)As	und	und	5000	159
GaAs	3	und	100	158
In(.20)Ga(.80)AsN	3	und	60	157
GaAs	und	und	15	156
Al(.15)Ga(.85)As	und	und	30	155d
Al(.15)Ga(.85)As	P+	3.5E18	80	155c
Al(.15)Ga(.85)As	und	und	300	155b
Al(.15)Ga(.85)As	N+	3.5E18	80	155a
Al(0.7)Ga(0.3)As	N	1E17	700	154
GaAs	N+	3.5E18	2200	153
AlAs	und	und	1701	151
GaAs	3	und	696	152
AlAs	und	und	1701	151
GaAs Substrate		Si		149

NHFET
13

PHFET
11

FIG. 2A

FIG. 2B



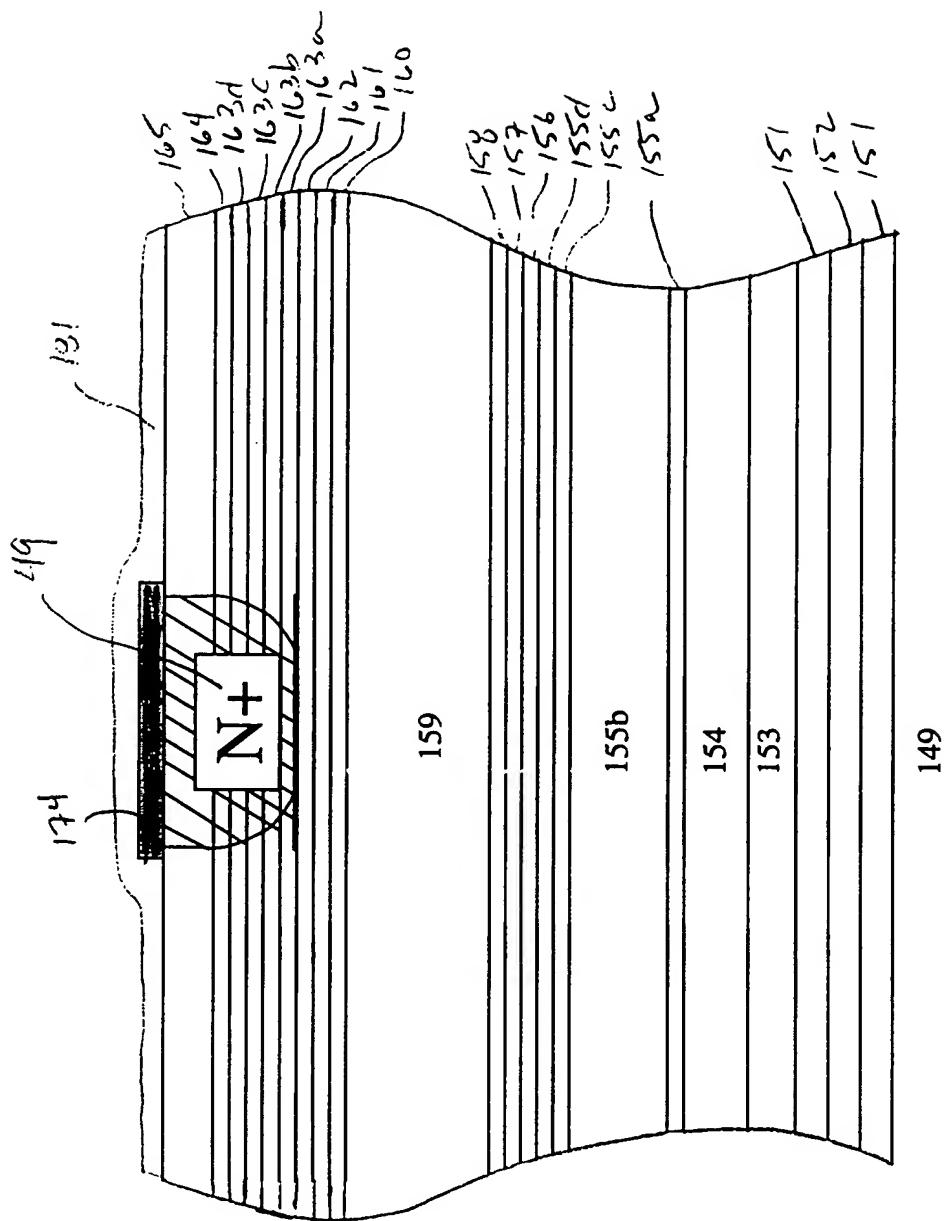


FIG. 34



FIG. 3B

FIG. 4

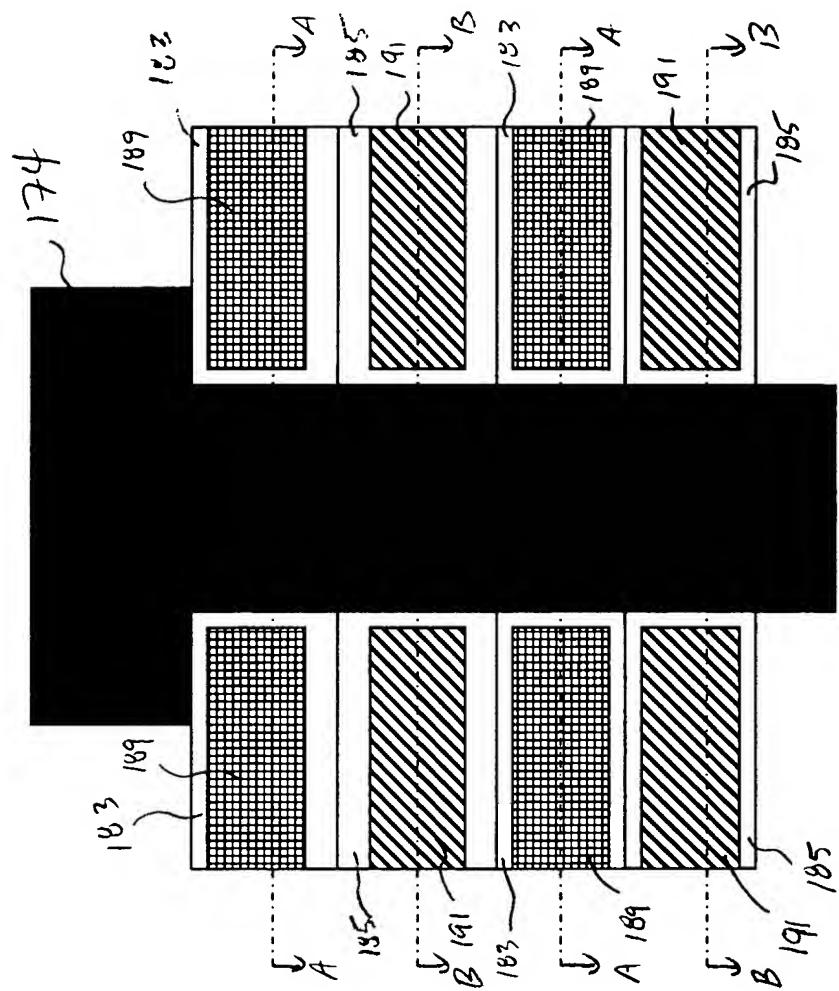


FIG. 5A

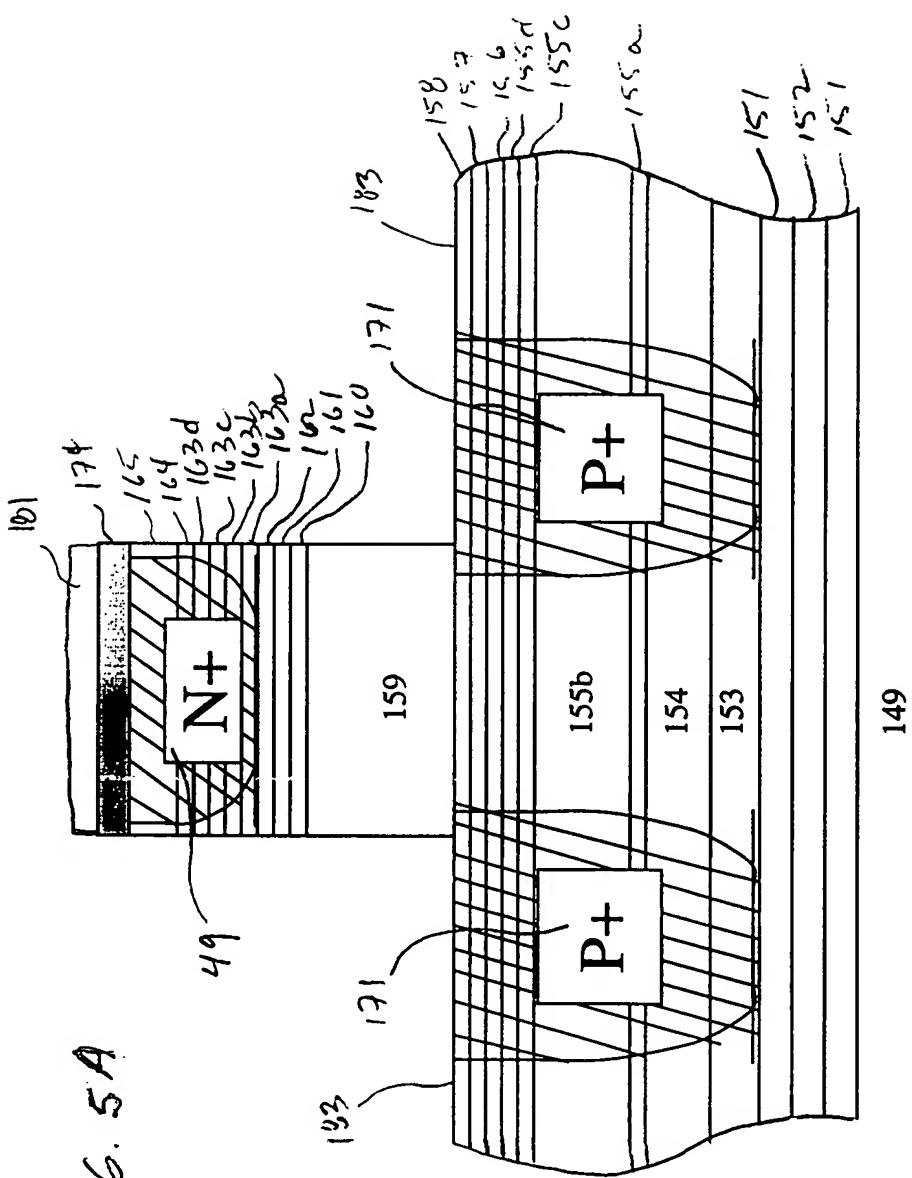
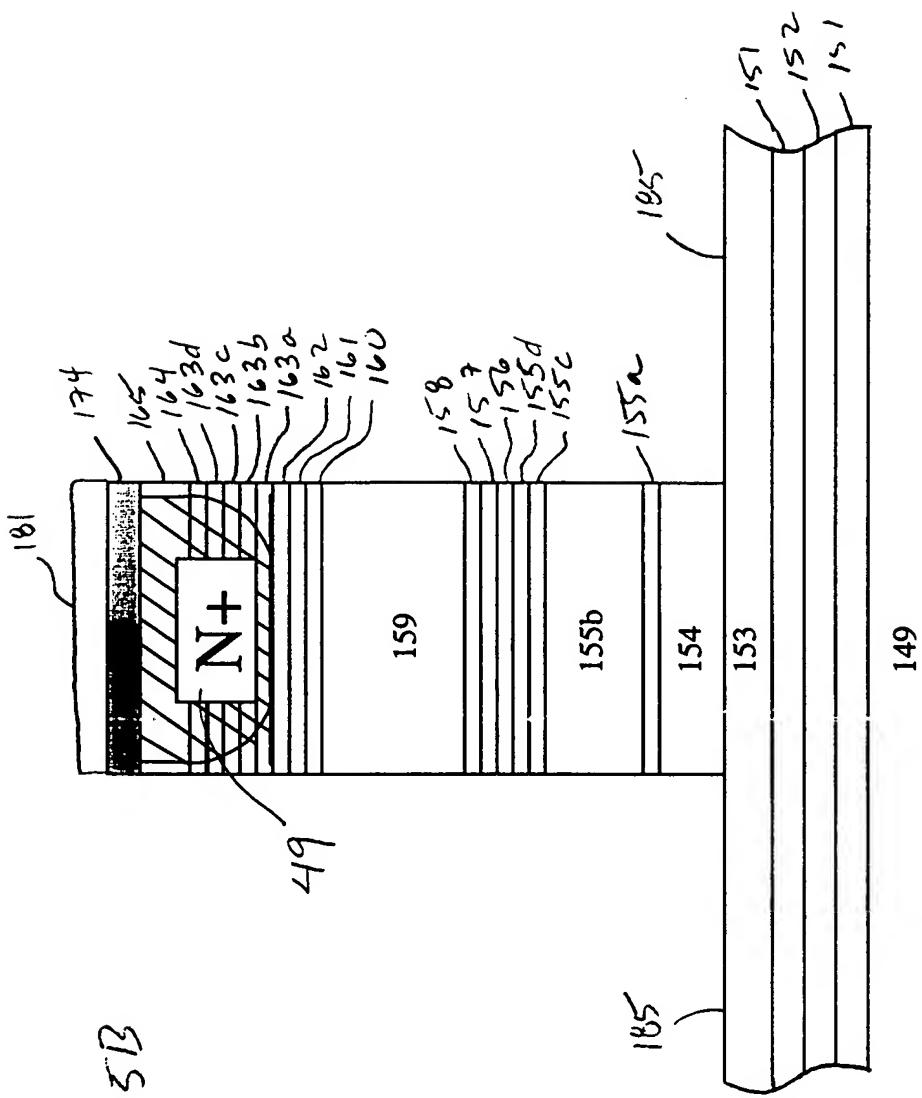


FIG. 5B



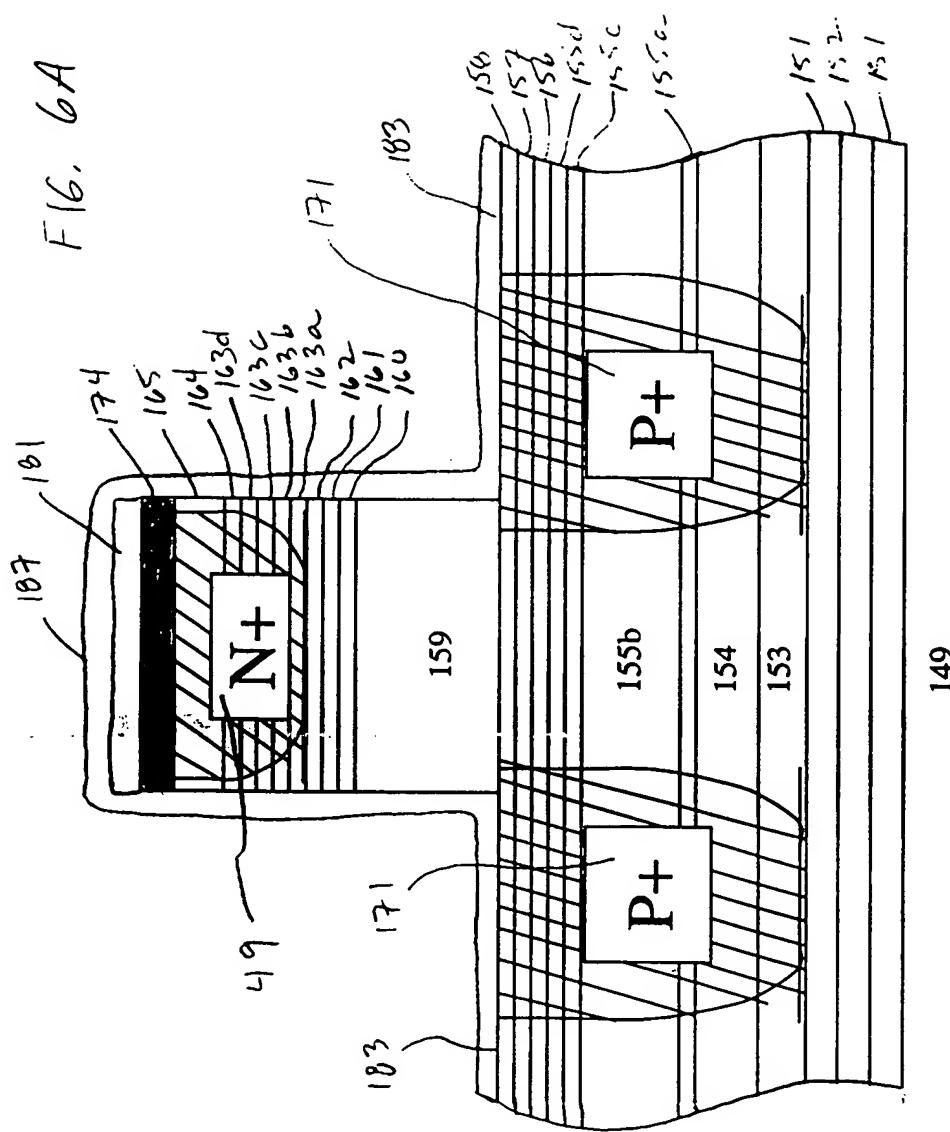
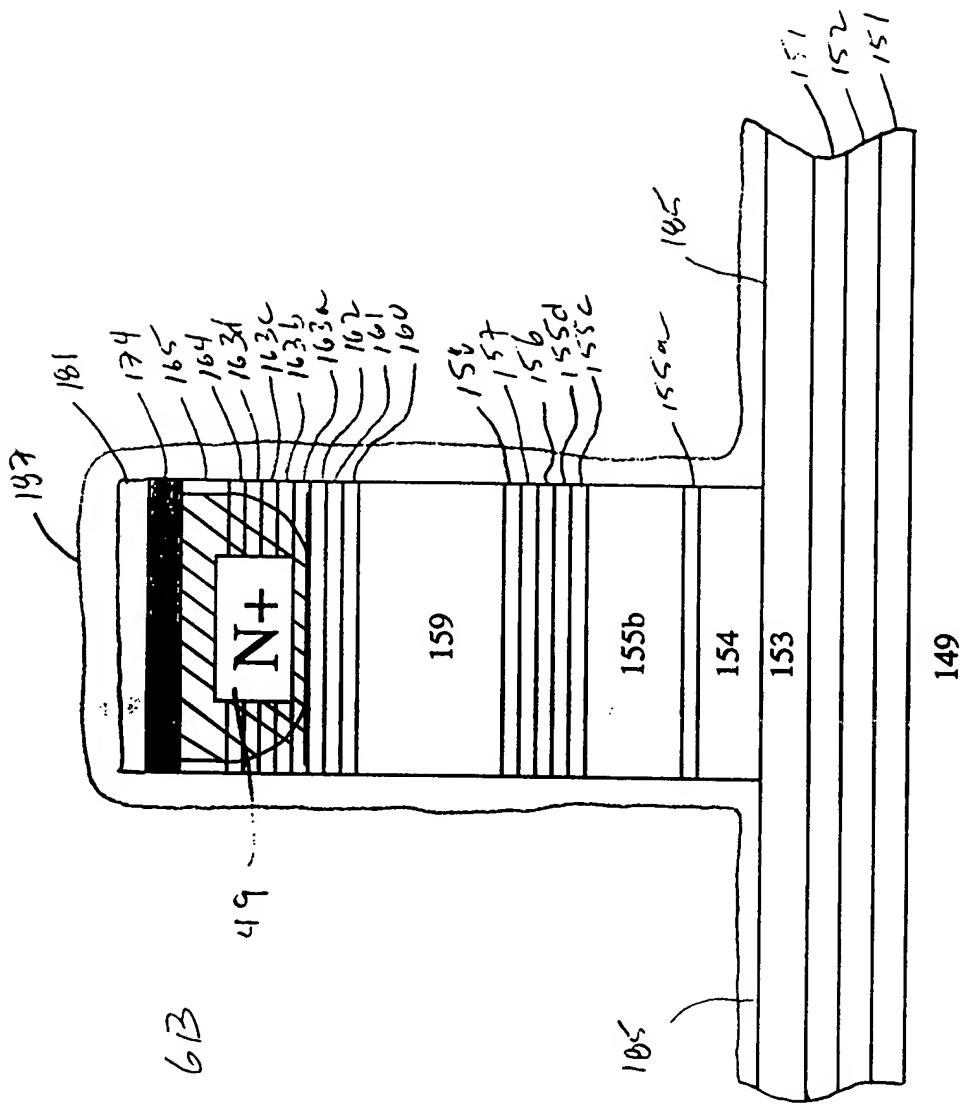
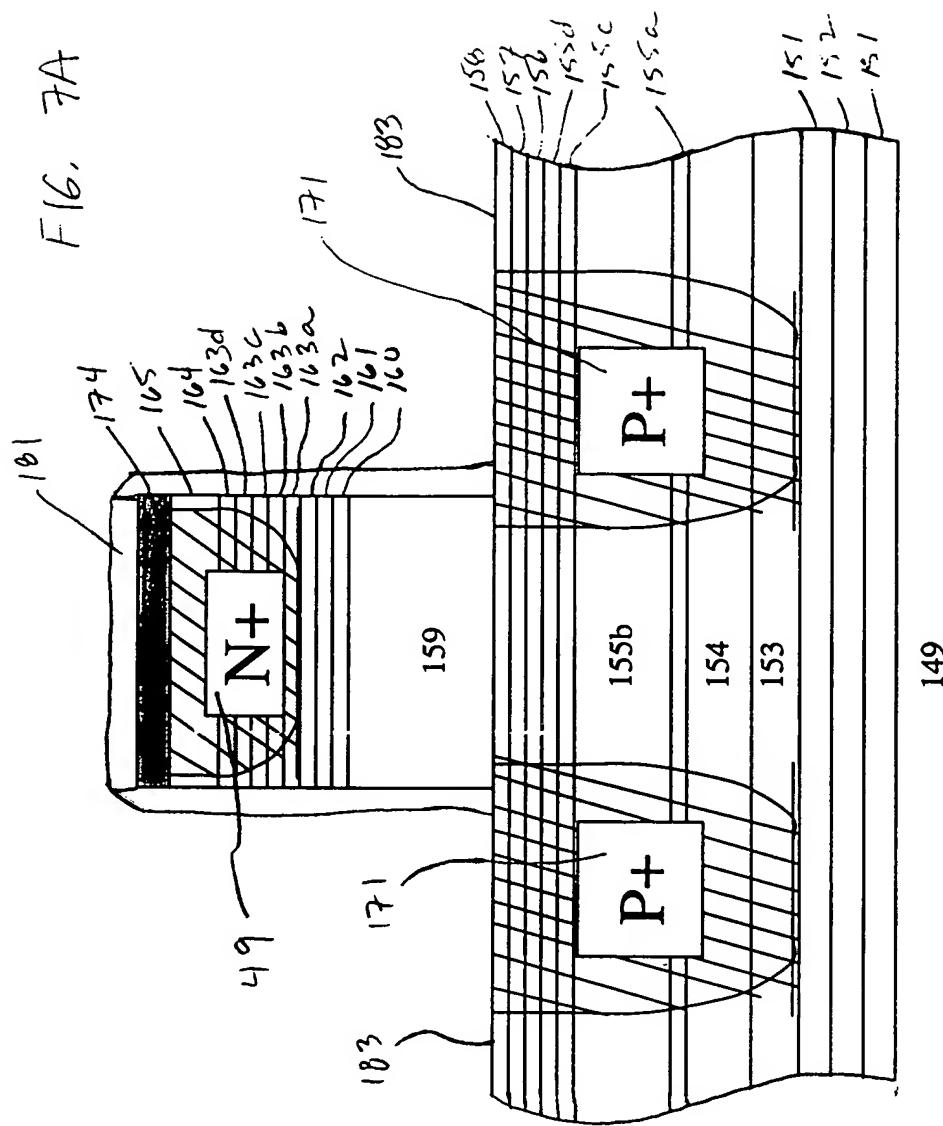


Fig. 613.



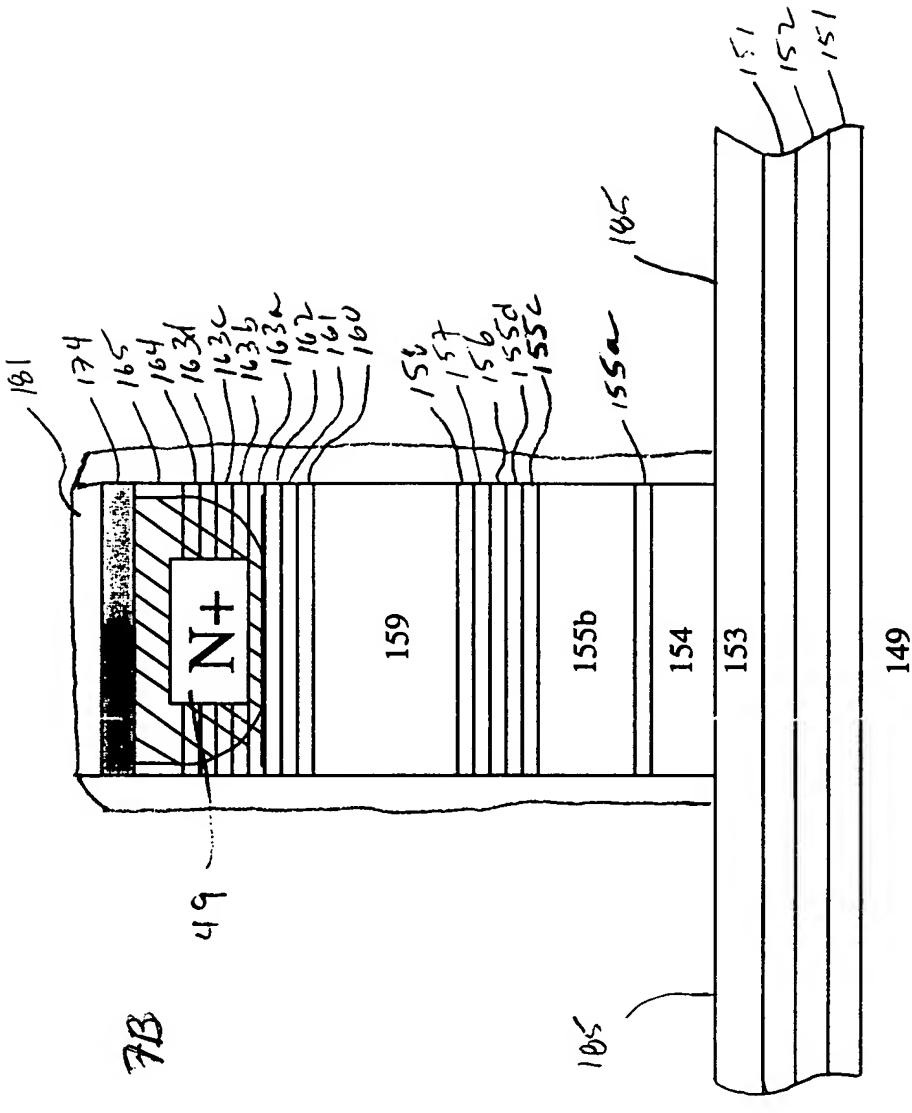
149



149

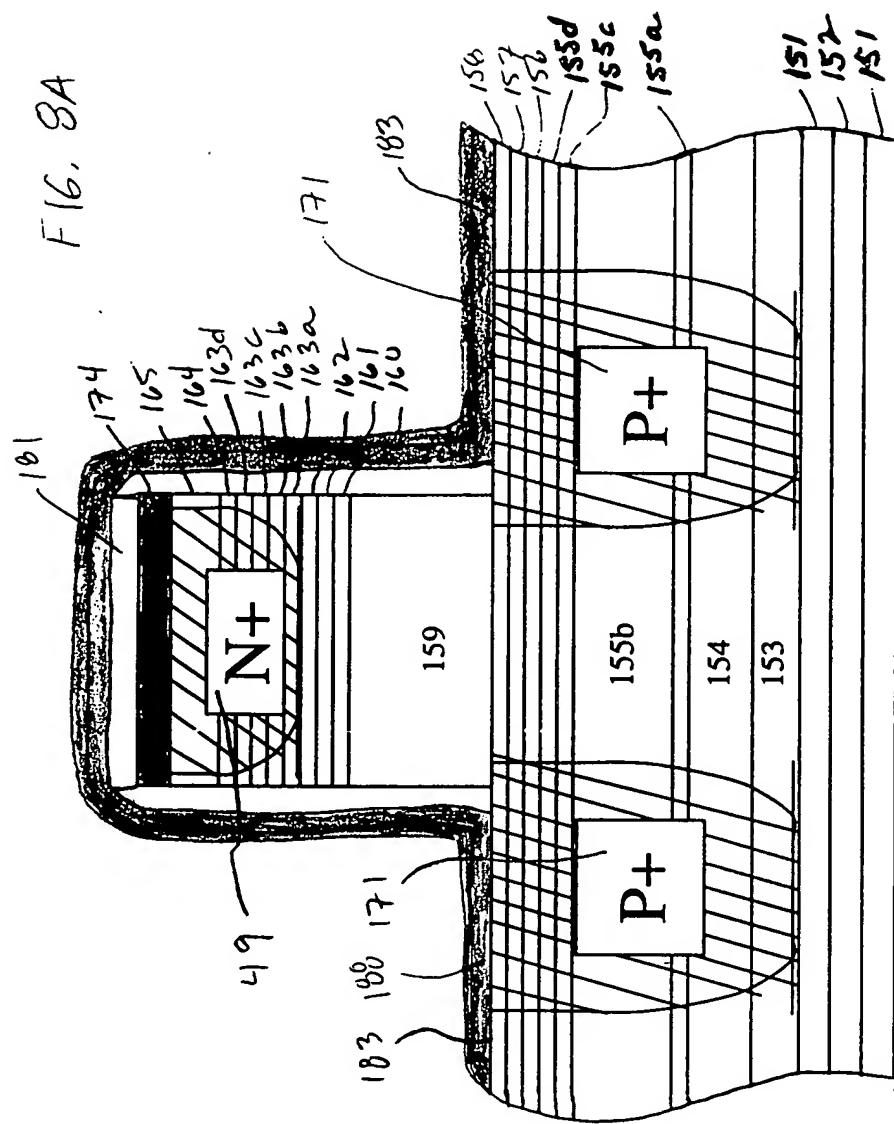
F16. 7B

49



149

F16. 8A



149

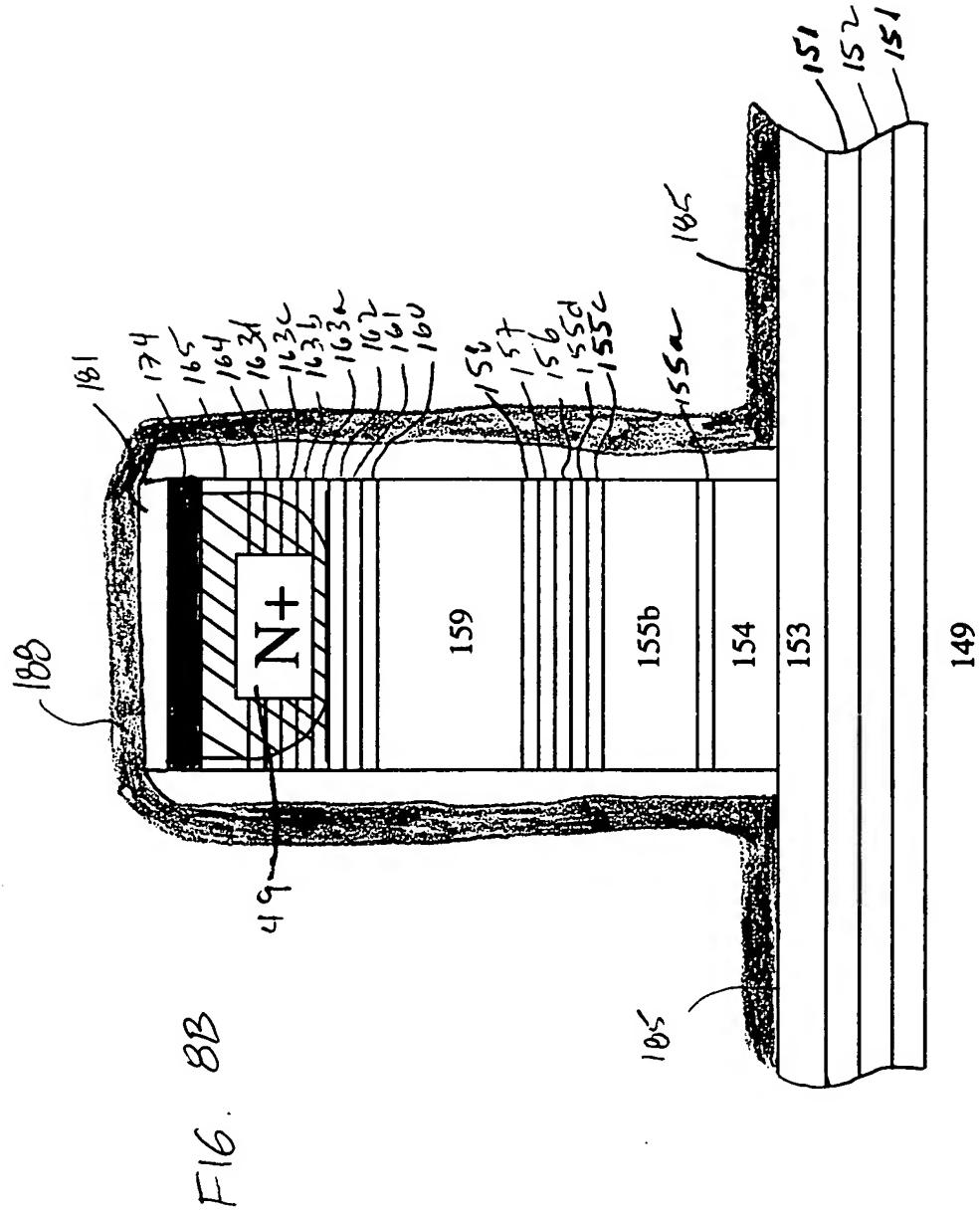
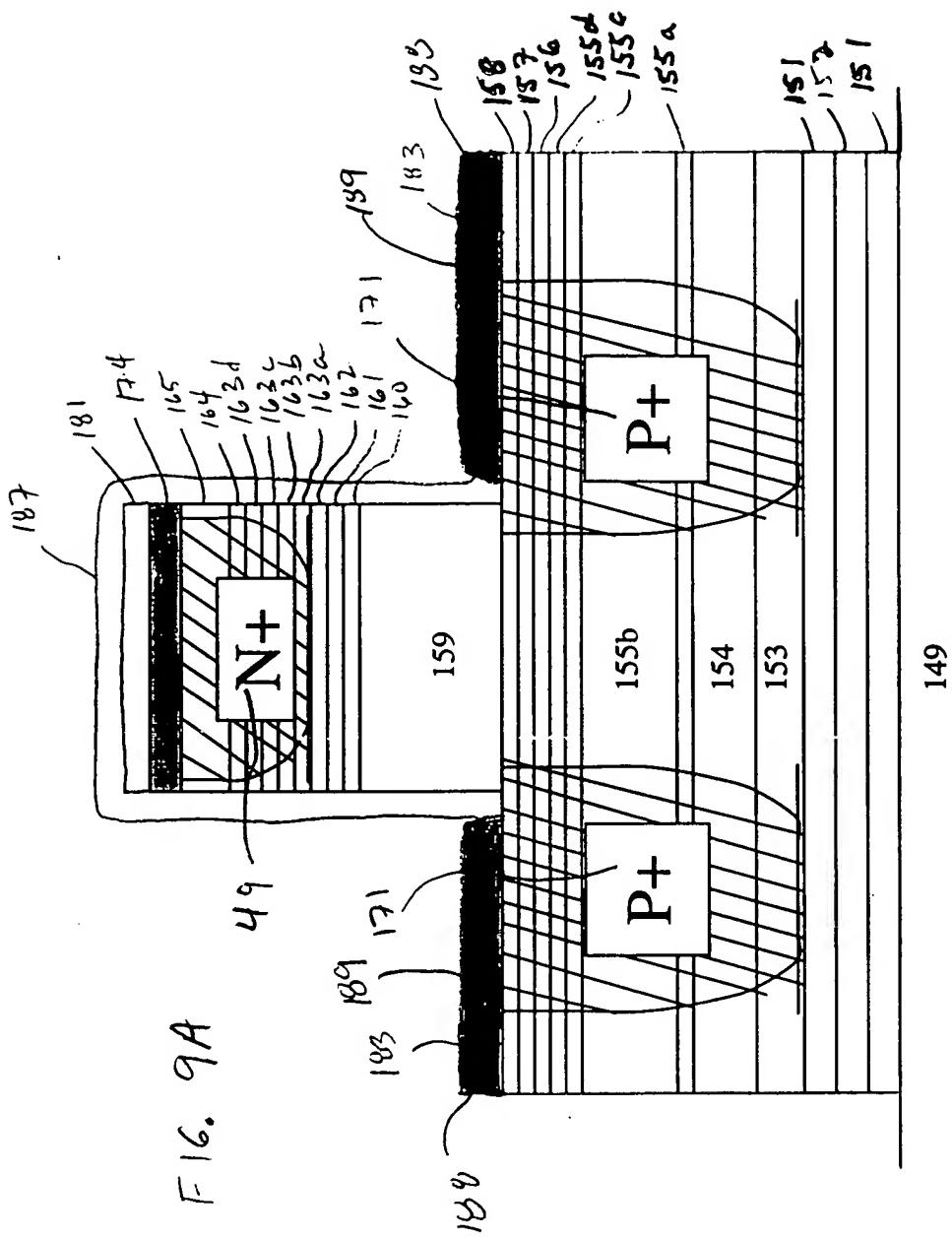
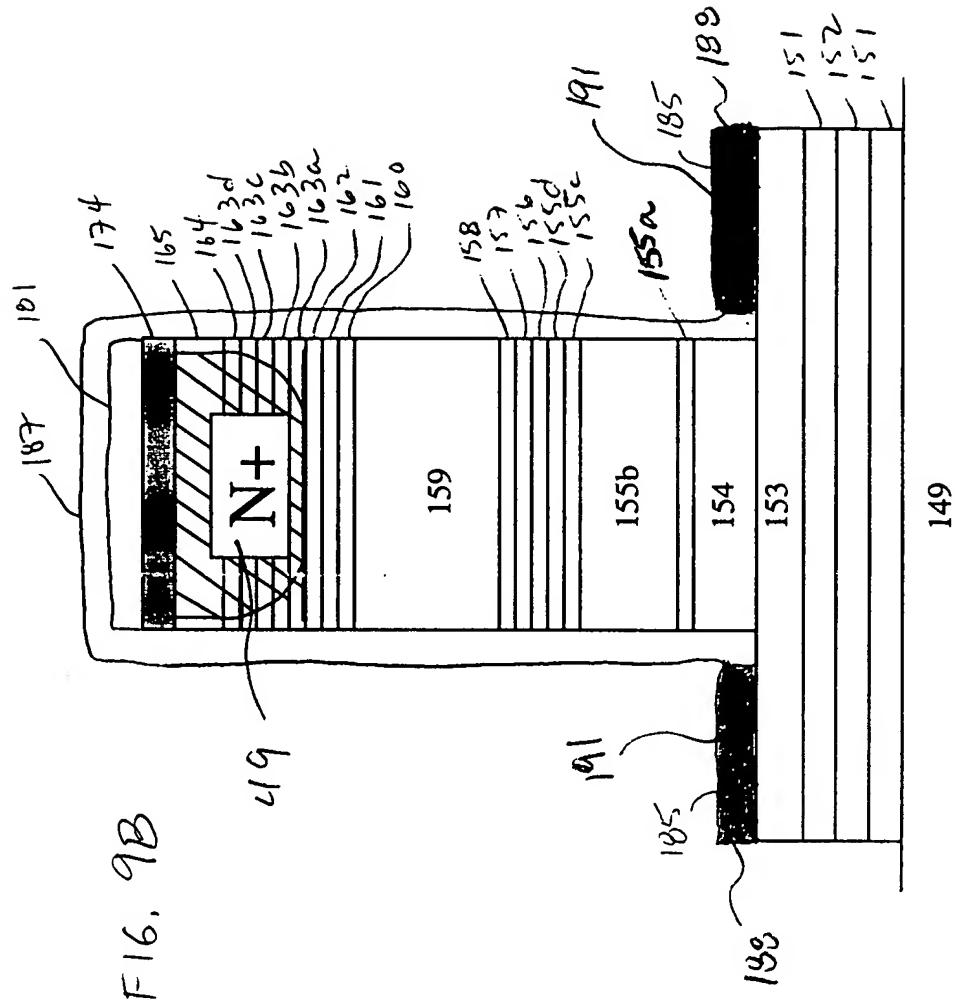


Fig. 8B.



149



F16, 9B

149

FIG. 10

